PMEG1030EH; PMEG1030EJ

10 V, 3 A ultra low V_F MEGA Schottky barrier rectifiers
Rev. 04 — 15 January 2010 Product d

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection encapsulated in small SMD plastic packages.

Table 1. **Product overview**

Type number	Package		Configuration
	NXP	JEITA	
PMEG1030EH	SOD123F	-	single isolated diodes
PMEG1030EJ	SOD323F	SC-90	single isolated diodes

1.2 Features

Forward current: 3 A Reverse voltage: 10 V

Ultra low forward voltage

Small and flat lead SMD package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switched-mode power supply
- Inverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	-	3	Α
V_R	reverse voltage		-	-	10	V
V_{F}	forward voltage	I _F = 3 A	<u>[1]</u> _	390	530	mV

[1] Pulse test: $t_0 \le 300 \ \mu s$; $\delta \le 0.02$.



PMEG1030EH; PMEG1030EJ

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2. Pinning information

Table 3. Pinning

10010 01	9	
Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	1 1 2 sym001
		001aab540

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	Package	Package			
	Name	Description	Version		
PMEG1030EH	-	plastic surface mounted package; 2 leads	SOD123F		
PMEG1030EJ	SC-90	plastic surface mounted package; 2 leads	SOD323F		

4. Marking

Table 5. Marking codes

Type number	Marking code
PMEG1030EH	AC
PMEG1030EJ	E7

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage		-	10	V
I _F	forward current	T _{sp} ≤ 55 °C	-	3	Α
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$	-	5.5	Α
I _{FSM}	non-repetitive peak forward current	t = 8 ms; square wave	[1] _	9	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PMEG1030EH		<u>[1]</u> -	375	mW
			[2] _	830	mW
	PMEG1030EJ		[1] -	360	mW
			[2] _	830	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air					
	PMEG1030EH		[1][2]	-	-	330	K/W
			[2][3]	-	-	150	K/W
	PMEG1030EJ		[1][2]	-	-	350	K/W
			[2][3]	-	-	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point						
	PMEG1030EH			-	-	60	K/W
	PMEG1030EJ			-	-	55	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

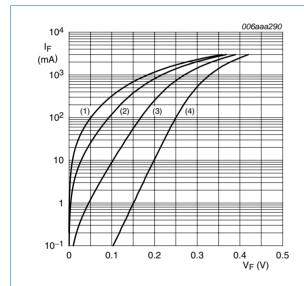
Characteristics 7.

Table 8. **Characteristics**

 $T_{amb} = 25 \, ^{\circ}\text{C}$ unless otherwise specified.

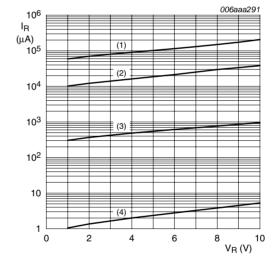
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
	$I_F = 0.01 A$	-	100	130	mV	
	I _F = 0.1 A	-	170	200	mV	
	I _F = 1 A	-	280	350	mV	
		I _F = 3 A	-	390	530	mV
I_R	reverse current	V _R = 5 V	-	0.55	2	mA
		V _R = 8 V	-	0.8	2.5	mA
		V _R = 10 V	-	1	3	mA
C_d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	70	85	рF

[1] Pulse test: $t_0 \le 300 \ \mu s$; $\delta \le 0.02$.



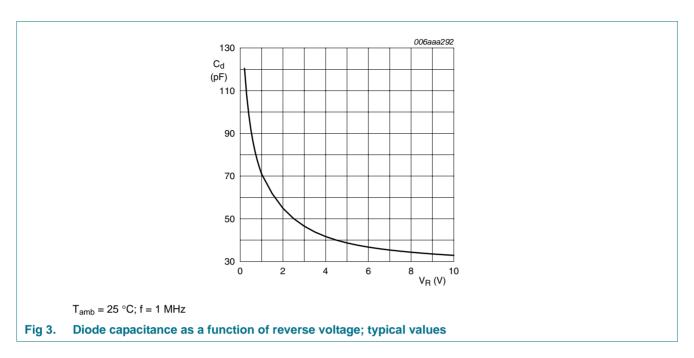
- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values

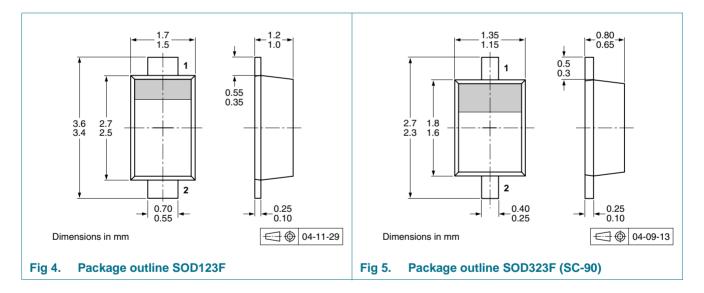


- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values



8. Package outline



9. Packing information

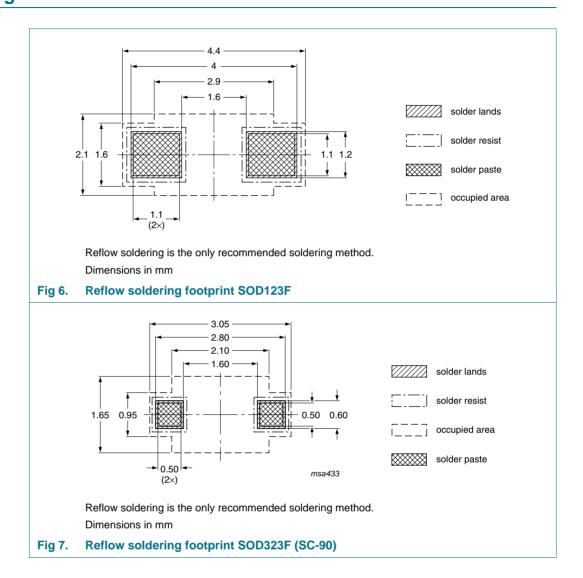
Table 9. Packing methods

The -xxx numbers are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	scription Packing quantity	
			3000	10000
PMEG1030EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135
PMEG1030EJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see <u>Section 13</u>.

10. Soldering



11. Revision history

Table 10. Revision history

Product data sheet

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG1030EH_EJ_4	20100115	Product data sheet	-	PMEG1030EH_EJ_3
Modifications:		eet was changed to reflect w legal definitions and disc		
PMEG1030EH_EJ_3	20050602	Product data sheet	-	PMEG1030EH_EJ_2
PMEG1030EH_EJ_2	20050405	Product data sheet	-	PMEG1030EJ_1
PMEG1030EJ_1	20050124	Product data sheet	-	-

7 of 9

PMEG1030EH; PMEG1030EJ

10 V, 3 A ultra low V_F MEGA Schottky barrier rectifiers

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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8 of 9

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NXP Semiconductors

PMEG1030EH; PMEG1030EJ

10 V, 3 A ultra low V_F MEGA Schottky barrier rectifiers

14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	3
6	Thermal characteristics	3
7	Characteristics	4
8	Package outline	5
9	Packing information	5
10	Soldering	ô
11	Revision history	7
12	Legal information	8
12.1	Data sheet status	8
12.2	Definitions	8
12.3	Disclaimers	8
12.4	Trademarks	8
13	Contact information	8
14	Contents	9

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